



## N-Channel Depletion-Mode Vertical DMOS FETs

### Features

- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

### Applications

- ▶ Normally-on switches
- ▶ Solid state relays
- ▶ Converters
- ▶ Linear amplifiers
- ▶ Constant current sources
- ▶ Power supply circuits
- ▶ Telecom

### Ordering Information

Device	Package Options		$BV_{DSX}/BV_{DGX}$ (V)	$R_{DS(ON)}$ (max) ( $\Omega$ )	$I_{DSS}$ (min) (mA)
	TO-92	TO-220			
DN2535	DN2535N3-G	DN2535N5-G	350	25	150

-G indicates package is RoHS compliant ('Green')



### Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	$BV_{DSX}$
Drain-to-gate voltage	$BV_{DGX}$
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

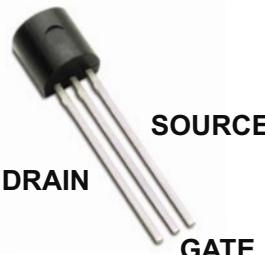
\* Distance of 1.6mm from case for 10 seconds.

### General Description

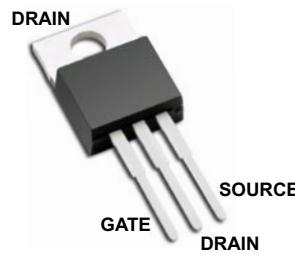
The Supertex DN2535 is a low threshold depletion mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

### Pin Configurations



3-Lead TO-92 (N3)



3-Lead TO-220 (N5)

### Product Marking



YY = Year Sealed  
WW = Week Sealed  
\_\_\_\_\_ = "Green" Packaging

3-Lead TO-92 (N3)



L = Lot Number  
YY = Year Sealed  
WW = Week Sealed  
\_\_\_\_\_ = "Green" Packaging

3-Lead TO-220 (N5)

## Thermal Characteristics

Package	I <sub>D</sub> (continuous) <sup>t</sup> (mA)	I <sub>D</sub> (pulsed) (mA)	Power Dissipation @T <sub>c</sub> = 25°C (W)	θ <sub>jc</sub> (°C/W)	θ <sub>ja</sub> (°C/W)	I <sub>DR</sub> (mA)	I <sub>DRM</sub> (mA)
TO-92	120	500	1.0	125	170	120	500
TO-220	500	500	15	8.3	70	500	500

**Notes:**

<sup>t</sup> I<sub>D</sub> (continuous) is limited by max rated T<sub>j</sub>

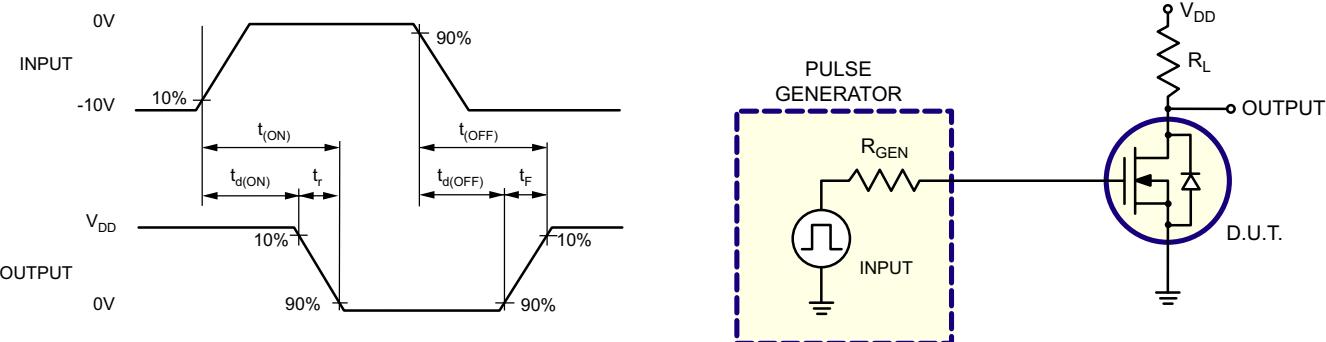
## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV <sub>DSX</sub>	Drain-to-source breakdown voltage	350	-	-	V	V <sub>GS</sub> = -5.0V, I <sub>D</sub> = 100μA
V <sub>GS(OFF)</sub>	Gate-to-source off voltage	-1.5	-	-3.5	V	V <sub>DS</sub> = 25V, I <sub>D</sub> = 10μA
ΔV <sub>GS(OFF)</sub>	Change in V <sub>GS(OFF)</sub> with temperature	-	-	-4.5	mV/°C	V <sub>DS</sub> = 25V, I <sub>D</sub> = 10μA
I <sub>GSS</sub>	Gate body leakage current	-	-	100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
I <sub>D(OFF)</sub>	Drain-to-source leakage current	-	-	10	μA	V <sub>DS</sub> = Max rating, V <sub>GS</sub> = -10V
		-	-	1.0	mA	V <sub>DS</sub> = 0.8 Max Rating, V <sub>GS</sub> = -10V, T <sub>A</sub> = 125°C
I <sub>DSS</sub>	Saturated drain-to-source current	150	-	-	mA	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V
R <sub>DS(ON)</sub>	Static drain-to-source on-state resistance	-	17	25	Ω	V <sub>GS</sub> = 0V, I <sub>D</sub> = 120mA
ΔR <sub>DS(ON)</sub>	Change in R <sub>DS(ON)</sub> with temperature	-	-	1.1	%/°C	V <sub>GS</sub> = 0V, I <sub>D</sub> = 120mA
G <sub>FS</sub>	Forward transconductance	-	325	-	mmho	V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA
C <sub>ISS</sub>	Input capacitance	-	200	300	pF	V <sub>GS</sub> = -10V, V <sub>DS</sub> = 25V, f = 1.0MHz
C <sub>OSS</sub>	Common source output capacitance	-	12	30		
C <sub>RSS</sub>	Reverse transfer capacitance	-	1.0	5.0		
t <sub>d(ON)</sub>	Turn-on delay time	-	-	10	ns	V <sub>DD</sub> = 25V, I <sub>D</sub> = 150mA, R <sub>GEN</sub> = 25Ω,
t <sub>r</sub>	Rise time	-	-	15		
t <sub>d(OFF)</sub>	Turn-off delay time	-	-	15		
t <sub>f</sub>	Fall time	-	-	20		
V <sub>SD</sub>	Diode forward voltage drop	-	-	1.8	V	V <sub>GS</sub> = -10V, I <sub>SD</sub> = 120mA
t <sub>rr</sub>	Reverse recovery time	-	800	-	ns	V <sub>GS</sub> = -10V, I <sub>SD</sub> = 1.0A

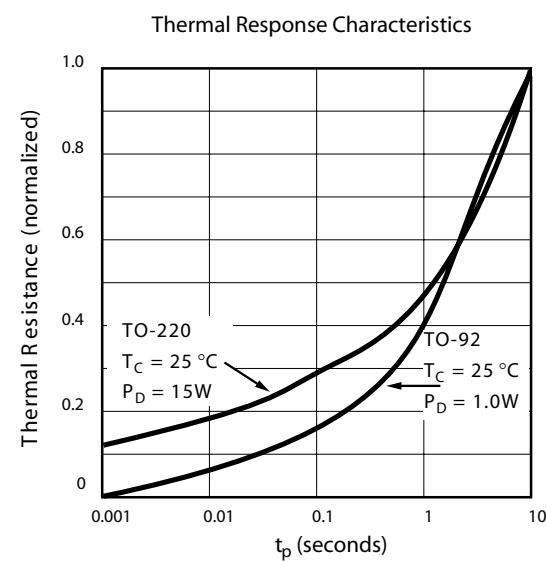
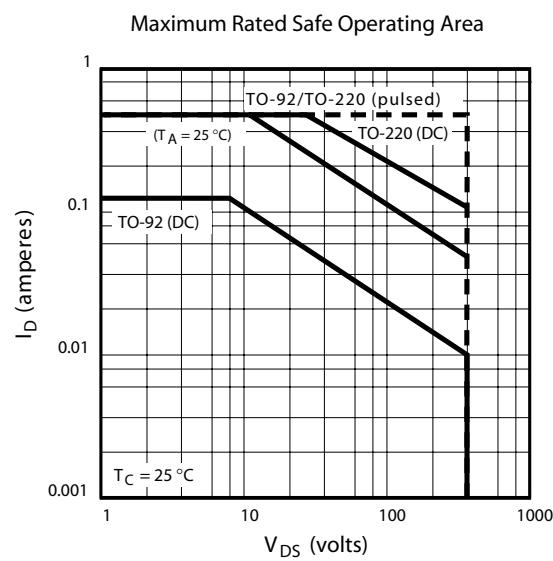
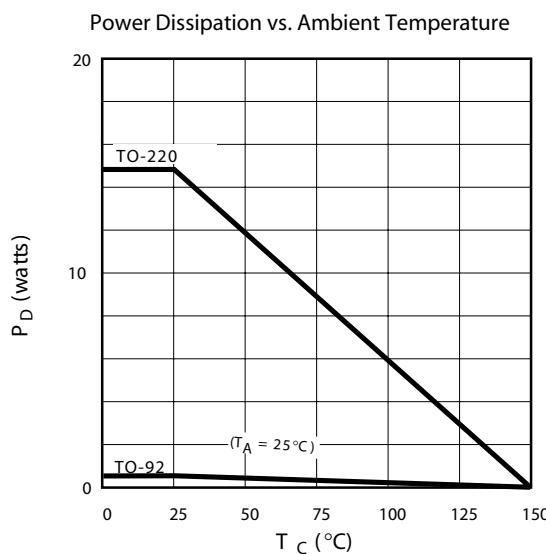
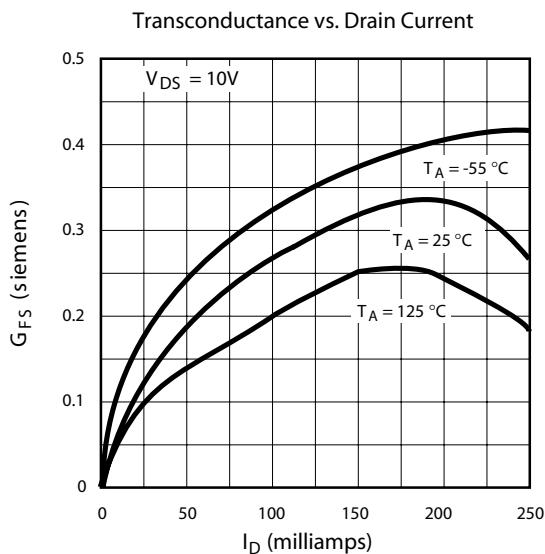
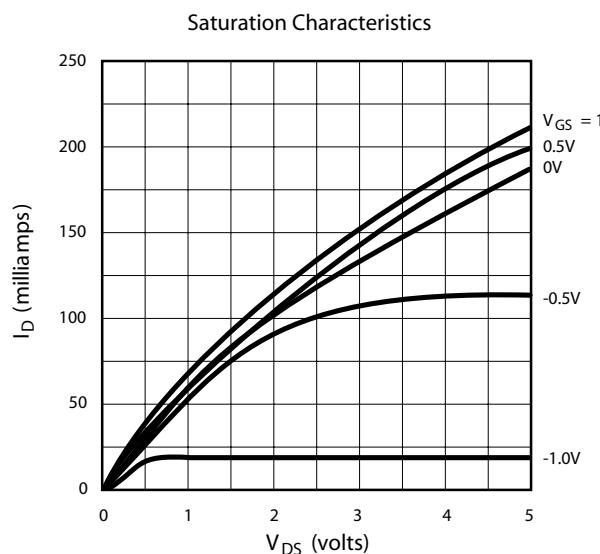
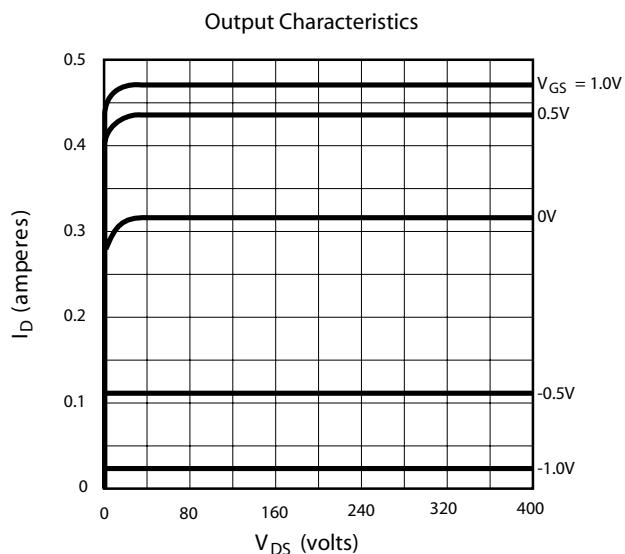
**Notes:**

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

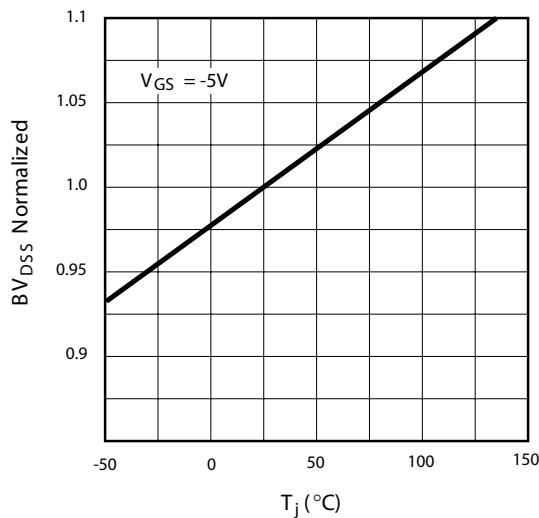
## Switching Waveforms and Test Circuit



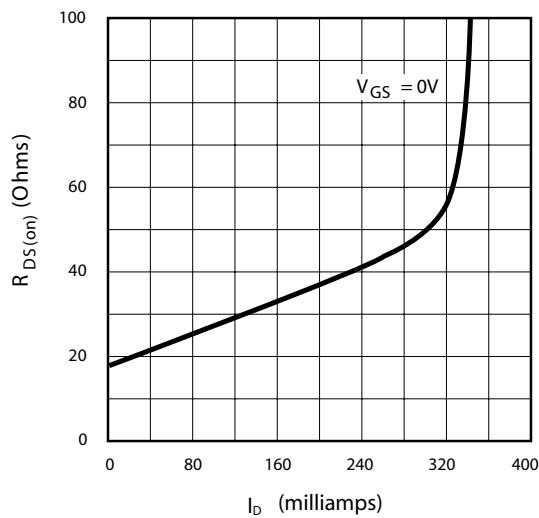
## Typical Performance Curves



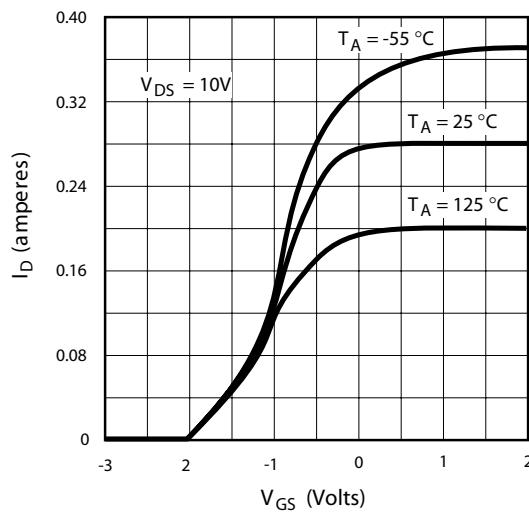
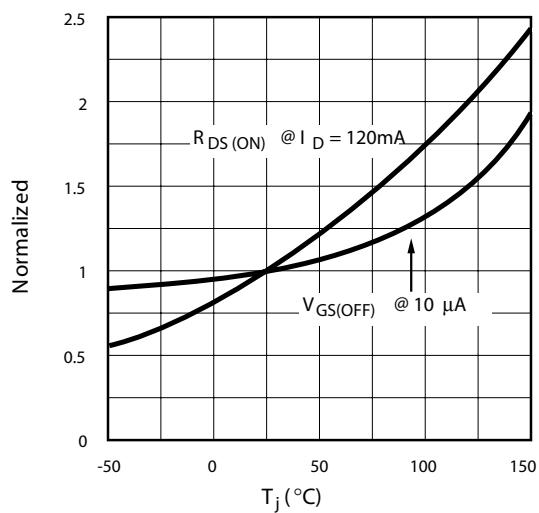
## Typical Performance Curves (cont.)

BV<sub>DSS</sub> Variation with Temperature

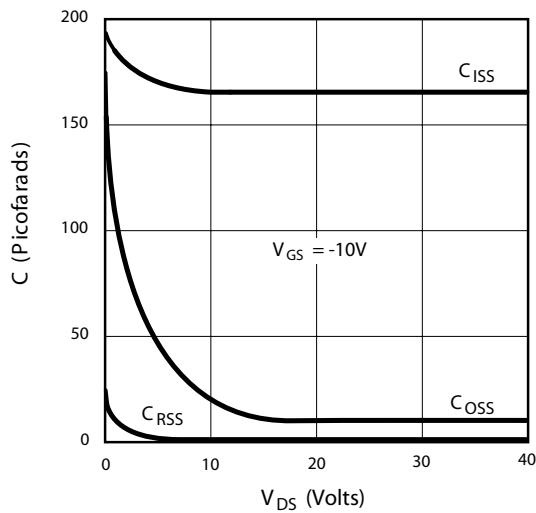
On-Resistance vs. Drain Current



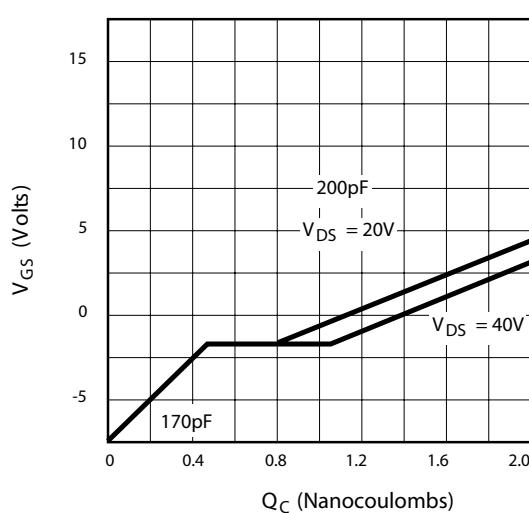
Transfer Characteristics

 $V_{GS(off)}$  and  $R_{DS}$  Variation with Temperature

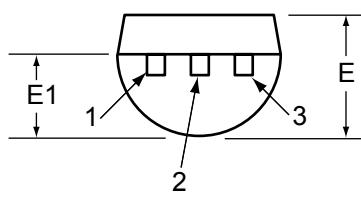
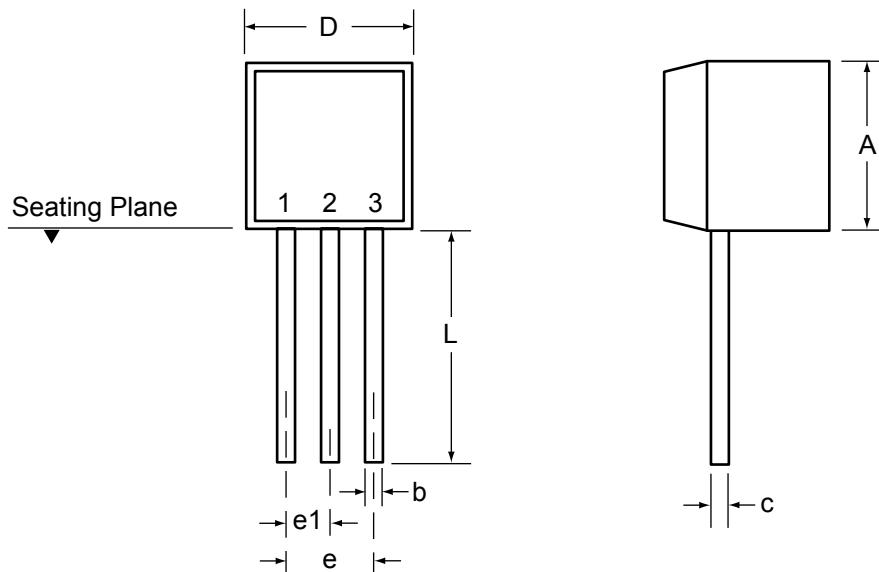
Capacitance Vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics



## 3-Lead TO-92 Package Outline (L/LL/N3)



Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 <sup>†</sup>	.022 <sup>†</sup>	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

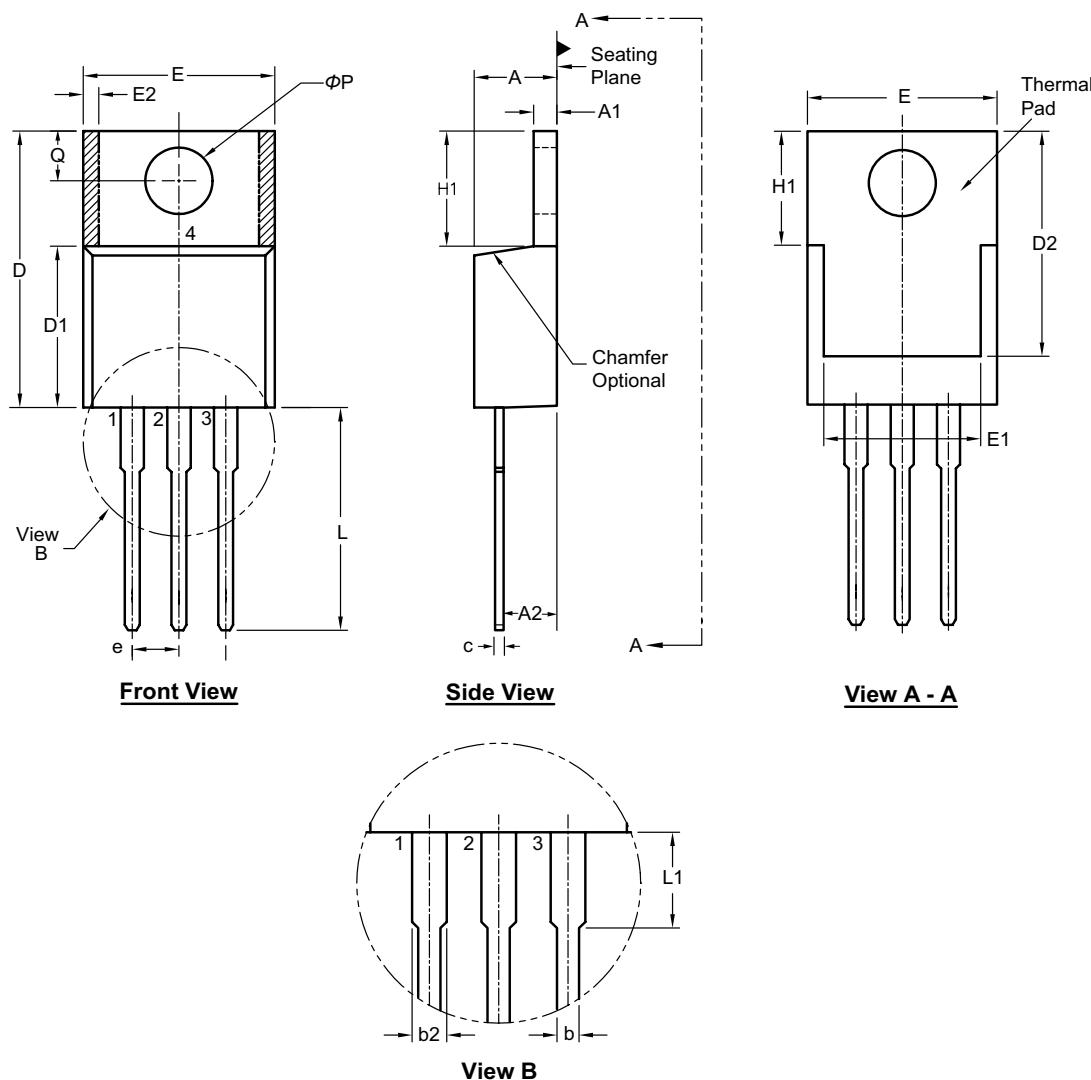
\* This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

<sup>†</sup> This dimension is a non-JEDEC dimension.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version D080408.

## 3-Lead TO-220 Package Outline (N5)



Symbol	A	A1	A2	b	b2	c	D	D1	D2	E	E1	E2	e	H1	L	L1	Q	ΦP	
Dimen- sion (inches)	MIN	.140	.020	.080	.015	.045	.012 <sup>t</sup>	.560	.326 <sup>t</sup>	.474 <sup>t</sup>	.380	.270	0.20*	.100 BSC	.230	.500	.200*	.100	.139
	NOM	-	-	-	.027	.057	-	-	-	-	-	-	-		-	-	-	-	
	MAX	.190	.055	.120 <sup>t</sup>	.040	.070	.024	.650	.361 <sup>t</sup>	.507	.420	.350	.030		.270	.580	.250	.135	.161

JEDEC Registration TO-220, Variation AB, Issue K, April 2002.

\* This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

<sup>t</sup> This dimension is a non-JEDEC dimension.

Drawings not to scale.

Supertex Doc. #: DSPD-3TO220N5, Version B090308.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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